MOS FET

SK8403190L

Panasonic

SK8403190L

Silicon N-channel MOS FET

For Load-switching / For DC-DC Converter

■ Features

- Low Drain-source On-state Resistance : RDS(on) typ = 10 m Ω (VGS = 4.5 V)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)
- Marking Symbol : 19

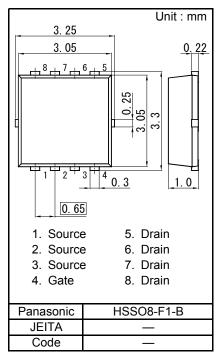
■ Packaging

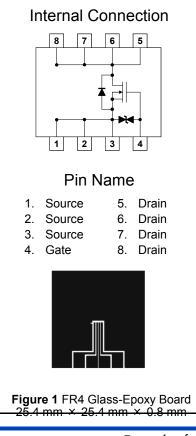
Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter			Symbol	Rating	Unit	
Drain to Source Voltage			VDS	30	V	
Gate to Source	Voltag	е	VGS	±20	V	
	Ta = 25 °C, t = 10 s *1		. ID	14		
Drain Current	Ta = 25 °C, DC *1			10	۸	
	Tc = 2	Tc = 25 °C		19	Α	
	Pulsed	d, Tch < 150 °C ^{*2}		42		
Total Power		Ta = 25 °C, DC *1	PD	2	W	
Dissipation		Tc = 25 °C	FD	19] vv	
Thermal Resistance		Channel to Ambient	Rth(ch-a)	62.5	°C / W	
memiai Resisi	ance	Channel to Case	Rth(ch-c)	6.6	-C / W	
Channel Temperature			Tch	150		
Operating ambient temperature			Topr	-40 to +85	°C	
Storage Temperature Range			Tstg	-55 to +150		
Avalanche Curi	Avalanche Current (Single pulse) *3			7	Α	
Avalanche Energy (Single pulse) *3			EAR	6	mJ	

- Note *1 Device mounted on a glass-epoxy board in Figure 1
 - *2 Pulse test: Ensure that the channel temperature does not exceed 150 °C
 - *3 VDD = 24 V, VGS = 10 to 0 V, L = 0.1 mH, Tch = 25 $^{\circ}$ C (initial)





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■ Electrical Characteristics Ta = 25 °C ± 3 °C

Static Characteristics

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	30			V
Zero Gate Voltage Drain Current	IDSS	VDS = 30 V, VGS = 0 V			10	μΑ
Gate-source Leakage Current	IGSS	VGS = ±16 V, VDS = 0 V			±10	μΑ
Gate-source Threshold Voltage	Vth	ID = 1.01 mA, VDS = 10 V	1		3	V
Drain-source On-state Resistance	RDS(on)1	ID = 7 A, VGS = 10 V		7	10	mΩ
Diain-source Oil-state Resistance	RDS(on)2	ID = 7 A, VGS = 4.5 V		10	14	

Dynamic Characteristics

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input Capacitance	Ciss	VDS = 10 V VCS = 0 V		780	1 092	
Output Capacitance	Coss	VDS = 10 V, VGS = 0 V f = 1 MHz		160	224	pF
Reverse Transfer Capacitance	Crss			61	98	
Turn-on Delay Time *1	td(on)	VDD = 15 V, VGS = 0 to 10 V		7		no
Rise Time *1	tr	ID = 7 A		3		ns
Turn-off Delay Time *1	td(off)	VDD = 15 V, VGS = 10 to 0 V		34		no
Fall Time *1	tf	ID = 7 A		4		ns
Total Gate Charge	Qg	VDD = 15 V VCS = 0 to 4 5 V		6.3		
Gate to Source Charge	Qgs	VDD = 15 V, VGS = 0 to 4.5 V ID = 7 A		2.5		nC
Gate to Drain Charge	Qgd	ID - 1 A		2.1		
Gate resistance	rg	f = 5 MHz		1.2	3	Ω

Body Diode Characteristic

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Diode Forward Voltage	VSD	IS = 7 A, VGS = 0 V		8.0	1.2	V

Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

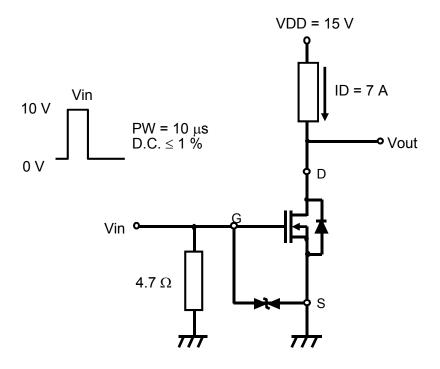
^{2. *1} Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

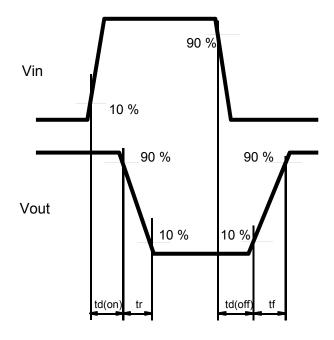
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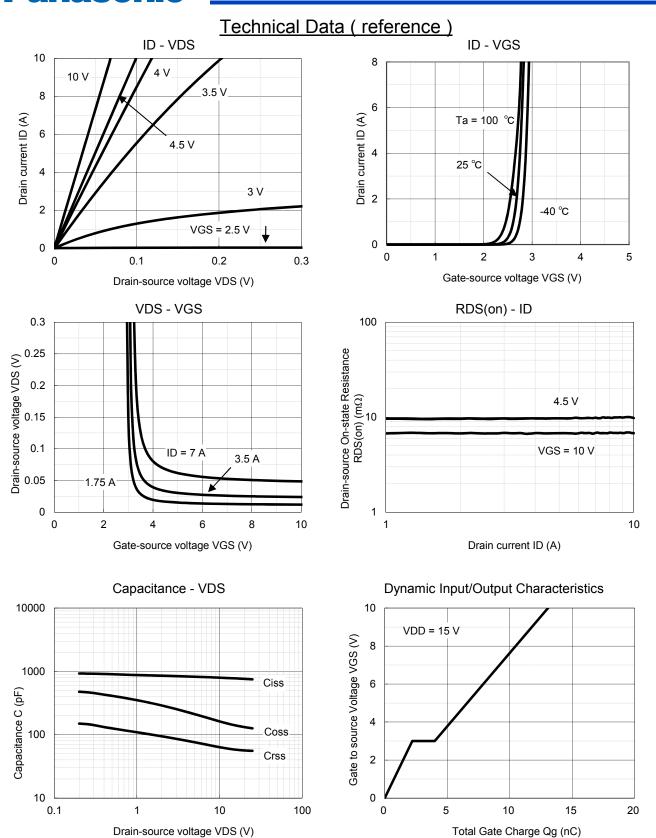
*1 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time





Established: 2012-09-08 : 2014-10-30 Revised

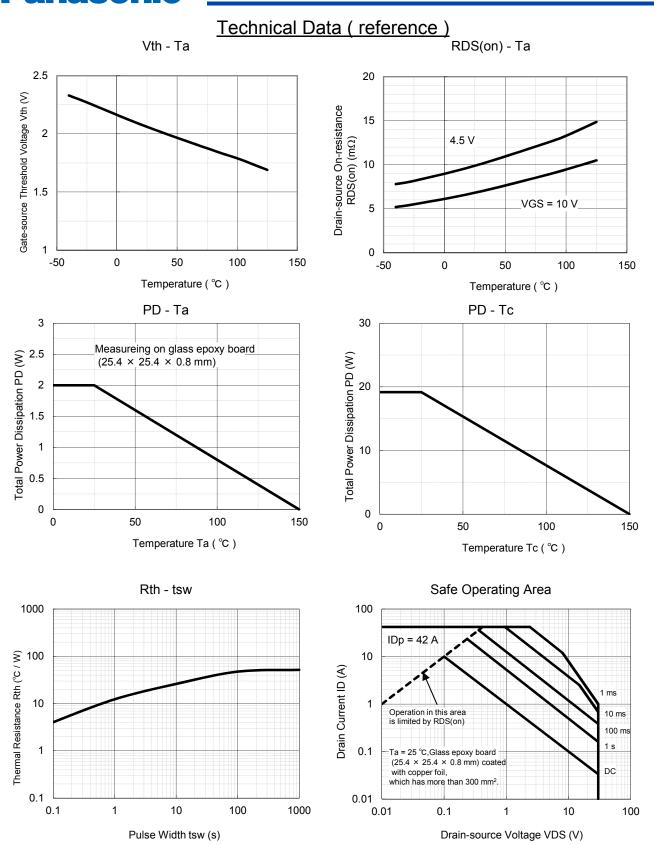
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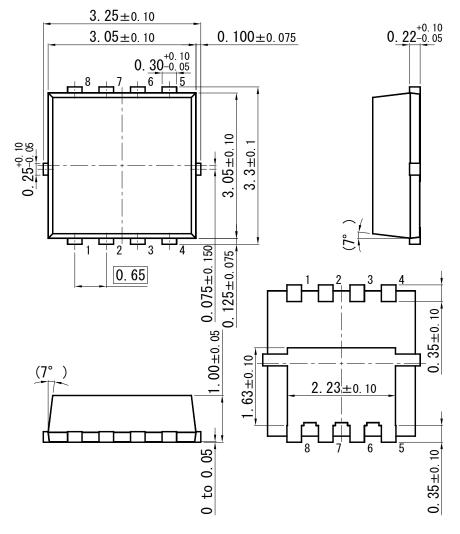
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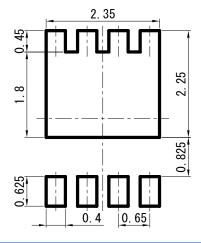
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HSSO8-F1-B

Unit: mm



■ Land Pattern (Reference) (Unit : mm)



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